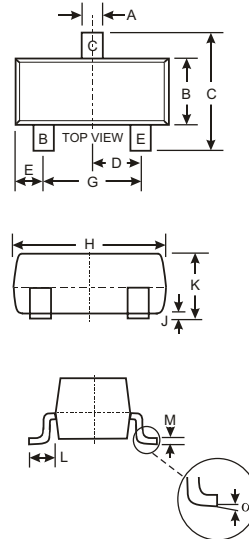


Features

- High current capacity in compact package.
- Epitaxial planar type.
- NPN complement:SS8050
- We declare that the material of product compliance with RoHS requirements.
- Marking Code:Y2



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	-25	V
Collector-Base Voltage	V _{CBO}	-40	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-1500	mAdc

• THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,(1) T _A =25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance,Junction to Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate,(2) T _A =25°C Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance,Junction to Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _j , T _{stg}	-55 to +150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

PNP SILICON GENERAL PURPOSE TRANSISTOR

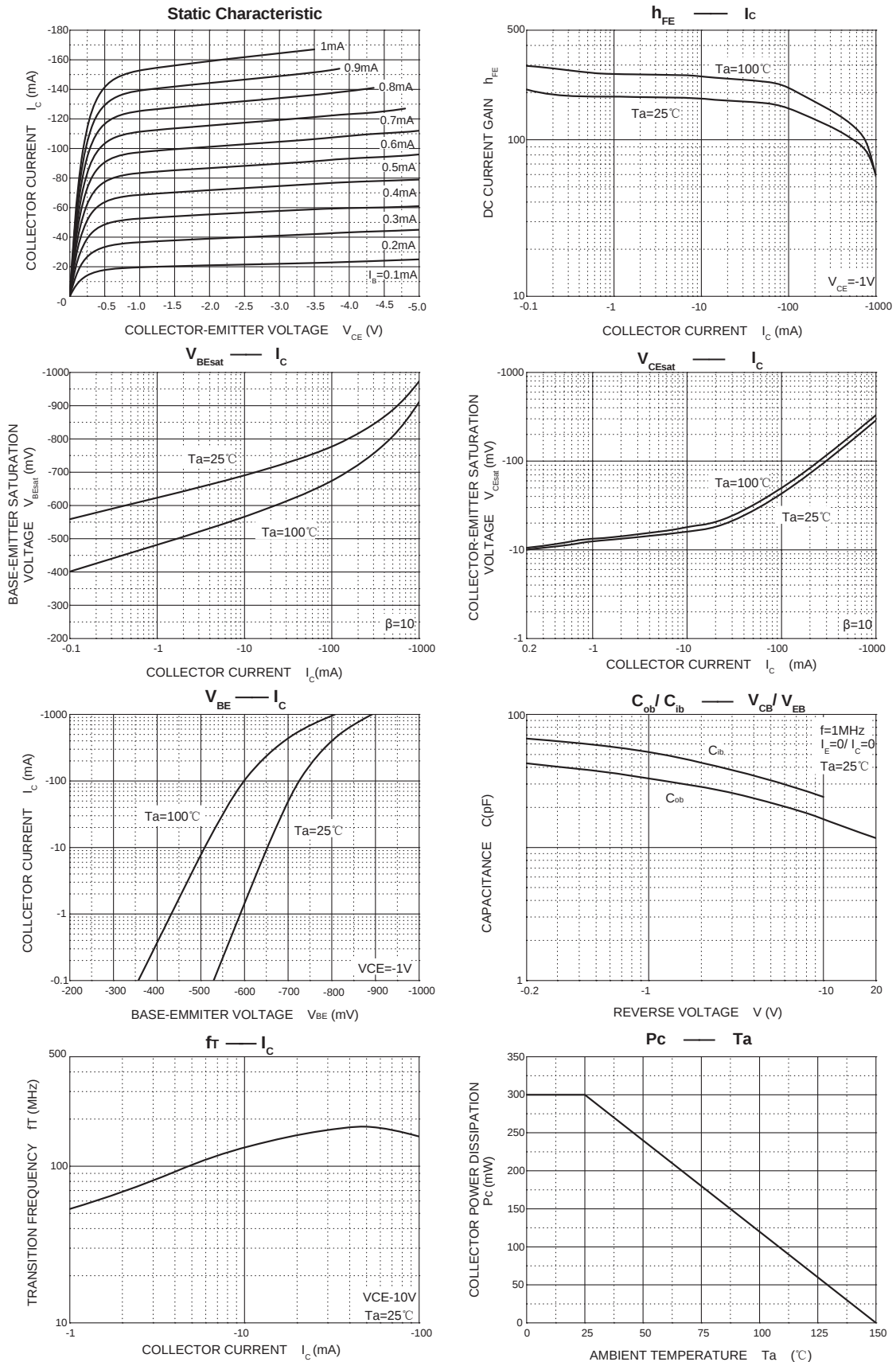
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1.0\text{mA}, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	120		400	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{mA}, I_B = -80\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800\text{mA}, I_B = -80\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{V},$ $I_C = -50\text{mA}, f = 30\text{MHz}$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			20	pF

CLASSIFICATION OF h_{FE}

Rank	C	D	E
Range	120-200	200-350	300-400

TYPICAL TRANSIENT CHARACTERISTICS



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